

Amendments To The Claims

1. (Currently Amended) A process for fabricating a semiconductor structure, comprising:
 - depositing a nitride layer on a semiconductor substrate with a first tool, wherein the nitride layer comprises silicon and nitrogen; and
 - depositing an anti-reflective layer on the semiconductor substrate with the first tool;

wherein the depositing of the anti-reflective layer comprises reacting SiH₂Cl₂, NH₃, and N₂O.
2. (Original) The process of claim 1, wherein the depositing of the nitride layer occurs before the depositing of the anti-reflective layer.
3. (Original) The process of claim 1, wherein the depositing of the anti-reflective layer occurs before the depositing of the nitride layer.
4. (Original) The process of claim 1, wherein the depositing of the nitride layer comprises reacting SiH₂Cl₂ and NH₃.
5. (Original) The process of claim 4, wherein the volumetric flow rate ratio for SiH₂Cl₂:NH₃ is from 0.3:1 to 5:1.
6. (Original) The process of claim 1, wherein the nitride layer comprises silicon deficient nitride.
7. (Original) The process of claim 1, wherein the nitride layer comprises silicon rich nitride.
8. (Original) The process of claim 1, wherein the nitride layer comprises a graded silicon nitride layer.
9. (Cancelled)
10. (Original) The process of claim 1, wherein the anti-reflective layer comprises silicon oxynitride.

11. (Original) The process of claim 1 further comprising depositing an oxide layer on the semiconductor substrate with a second tool, wherein the first tool and the second tool are the same.

12. (Original) The process of claim 11, wherein the depositing of the oxide layer comprises reacting SiH_2Cl_2 and N_2O .

13. (Original) The process of claim 1, wherein the first tool comprises a low-pressure chemical vapor deposition tool or a plasma-enhanced chemical vapor deposition tool.

14. (Original) The process for fabricating a semiconductor device, comprising:
forming a semiconductor structure by the process of claim 1; and
forming a semiconductor device from the semiconductor structure.

15. (Original) A process for making an electronic device comprising:
forming a semiconductor device by the process of claim 14; and
forming the electronic device comprising the semiconductor device.

16-23 (Cancelled)

24. (New) A process for fabricating a semiconductor structure, comprising:
depositing a nitride layer on a semiconductor substrate with a first tool, wherein the nitride layer comprises silicon and nitrogen; and
depositing an anti-reflective layer on the semiconductor substrate with the first tool;
wherein the anti-reflective layer comprises silicon-rich nitride.

25. (New) The process of claim 24, wherein the depositing of the nitride layer comprises reacting SiH_2Cl_2 and NH_3 .

26. (New) The process of claim 25, wherein the volumetric flow rate ratio for $\text{SiH}_2\text{Cl}_2:\text{NH}_3$ is from 0.3:1 to 5:1.

27. (New) The process of claim 24, wherein the nitride layer comprises silicon deficient nitride.

28. (New) The process of claim 24, further comprising depositing an oxide layer on the semiconductor substrate with the first tool, and
the depositing of the oxide layer comprises reacting SiH_2Cl_2 and N_2O .
29. (New) The process for fabricating a semiconductor device, comprising:
forming a semiconductor structure by the process of claim 24; and
forming a semiconductor device from the semiconductor structure.
30. (New) A process for making an electronic device comprising:
forming a semiconductor device by the process of claim 29; and
forming the electronic device comprising the semiconductor device.
31. (New) A process for fabricating a semiconductor structure, comprising:
depositing a nitride layer on a semiconductor substrate with a first tool, wherein
the nitride layer comprises silicon and nitrogen; and
depositing a SiO_2 layer on the semiconductor substrate with the first tool.
32. (New) The process of claim 31, wherein the depositing of the oxide layer
comprises reacting SiH_2Cl_2 and N_2O .